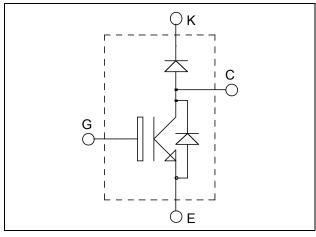
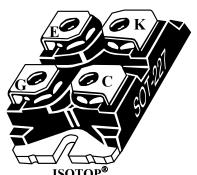


ISOTOP® Boost chopper Trench + Field Stop fast IGBT4 Power module





 $V_{CES} = 1200V$ $I_{C} = 25A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- Trench + Field Stop Fast IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Low leakage current
 - RBSOA and SCSOA rated

• Boost SiC Schottky Diode

- Zero reverse recovery
- Zero forward recovery
- Temperature Independent switching behavior
- Positive temperature coefficient on VF
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- ullet Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings @ $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
T	Continuous Collector Current	$T_C = 25^{\circ}C$	45	
I_{C}	Continuous Conector Current	$T_C = 80$ °C	25	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	50	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	170	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	50A @ 1100V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.7	2.05	2.4	V
$V_{CE(sat)}$		$I_C = 25A$ $T_j = 150$ °C		2.6		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 0.8 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics

·	Characteristic	Test Conditions		Min	Typ	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1430			
Coes	Output Capacitance				115		pF	
C_{res}	Reverse Transfer Capacitance	f = 1MHz			85			
Q_{G}	Gate charge	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 25A$			0.2		μС	
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		130			
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20			
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 600 V$ $I_{C} = 25 A$	$V_{CE} = 600V$ $V_{CE} = 25 A$		300		ns	
T_{f}	Fall Time	$R_G = 20\Omega$			45			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 25A$			150		ns	
T_{r}	Rise Time				35			
$T_{d(off)}$	Turn-off Delay Time				350			
$T_{\mathbf{f}}$	Fall Time	$R_G = 20\Omega$	1 ~		80			
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25$ °C		1.2		mJ	
Lon	Turn-on Switching Energy	$V_{CE} = 600V$	$T_J = 150$ °C		1.8		1113	
E_{off}	Turn-off Switching Energy	$I_C = 25A$ $R_G = 20\Omega$	- ,	$T_J = 25^{\circ}C$		1.5		mJ
Loff	Turn-on Switching Energy		$T_{\rm J} = 150^{\circ}{\rm C}$		2.2		1113	
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 900V$ $t_p \le 10 \mu s ; T_j = 150^{\circ} C$			100		A	

Chopper SiC diode ratings and characteristics

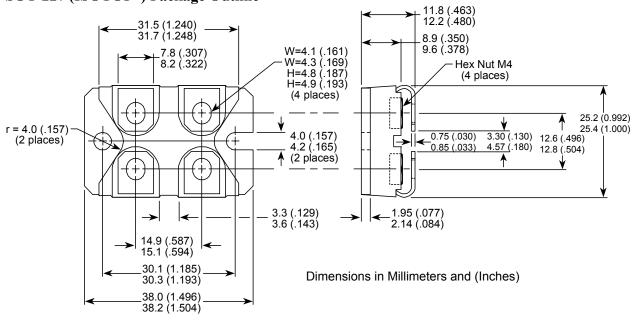
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
Ţ	Maximum Reverse Leakage Current	$V_{p}=1200V$	$T_j = 25^{\circ}C$		70	500	^
I_{RM}			$T_j = 175$ °C		200	700	μΑ
I_F	DC Forward Current		Tc = 125°C		15		A
V_{F}	Diode Forward Voltage	$I_F = 15A$	$T_i = 25^{\circ}C$		1.5	1.8	V
v _F	Diode Forward Voltage		$T_i = 175^{\circ}C$		2.2	3	V
Qc	Total Capacitive Charge	$I_F = 15A, V_R = 600V$ di/dt = 400A/ μ s			100		nC
С	Total Capacitance	$f = 1 MHz, V_R =$	IHz , $V_R = 400V$		74		рF
	Total Capacitance	$f = 1MHz, V_R =$	800V		54		hı.



Thermal and package characteristics

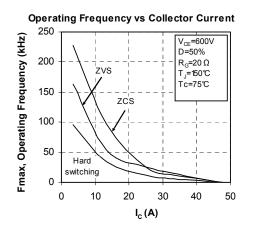
Symbol	Characteristic		Min	Тур	Max	Unit	
D	Junction to Case Thermal Resistance	IGBT			0.9	°C/W	
R_{thJC}		SiC Diode			1.1		
R_{thJA}	Junction to Ambient (IGBT & Diode)				20		
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		2500			V	
T_{J}, T_{STG}	Storage Temperature Range		-55		175	°C	
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300		
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m	
Wt	Package Weight			29.2		g	

SOT-227 (ISOTOP®) Package Outline

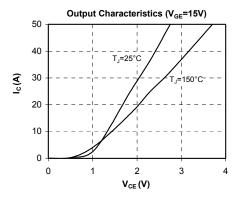


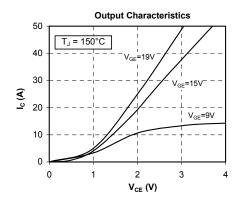
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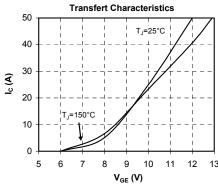
Typical Performance Curve

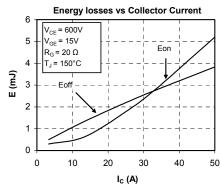


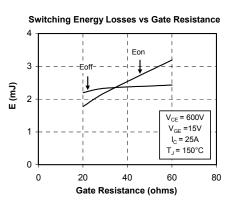


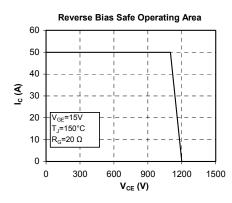


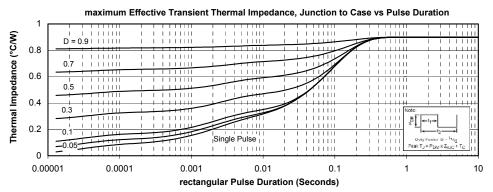












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